

HIGH CURRENT APPLICATION.

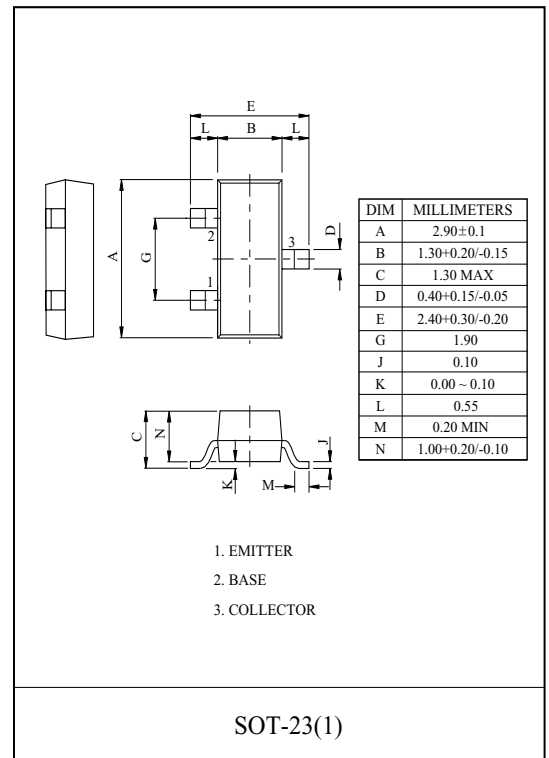
FEATURE

- Complementary to MPS8550SC.

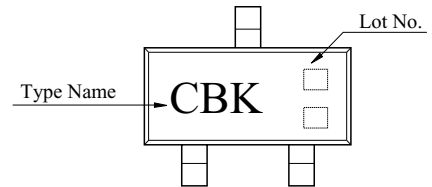
MAXIMUM RATING (Ta=25)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	1,200	mA
Collector Power Dissipation	P _C *	350	mW
Junction Temperature	T _j	150	
Storage Temperature Range	T _{stg}	-55 150	

* P_C : Package Mounted On 99.5% Alumina (10 × 8 × 0.6mm)



Marking



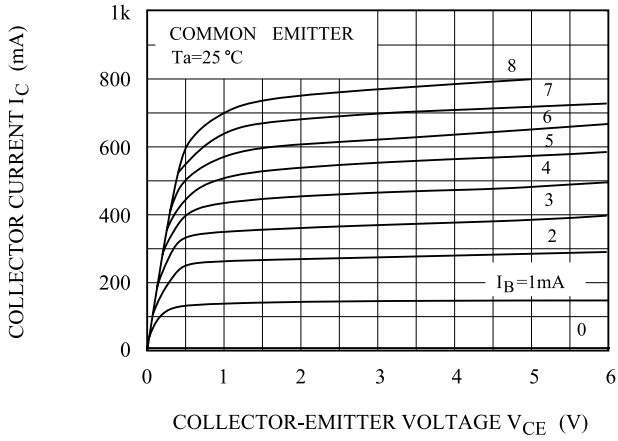
ELECTRICAL CHARACTERISTICS (Ta=25)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C =0.5mA, I _E =0	40	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	25	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =0.1mA, I _C =0	5	-	-	V
Collector Cut-off Current	I _{CBO}	V _{CB} =35V, I _E =0	-	-	0.1	uA
Emitter Cut-off Current	I _{EBO}	V _{EB} =4V, I _C =0	-	-	0.1	uA
DC Current Gain	h _{FE} (Note)	V _{CE} =1V, I _C =100mA	150	-	300	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =800mA, I _B =80mA	-	-	0.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =800mA, I _B =80mA	-	-	1.2	V
Transition Frequency	f _T	V _{CE} =6V, I _C =20mA, f=30MHz	150	-	-	MHz

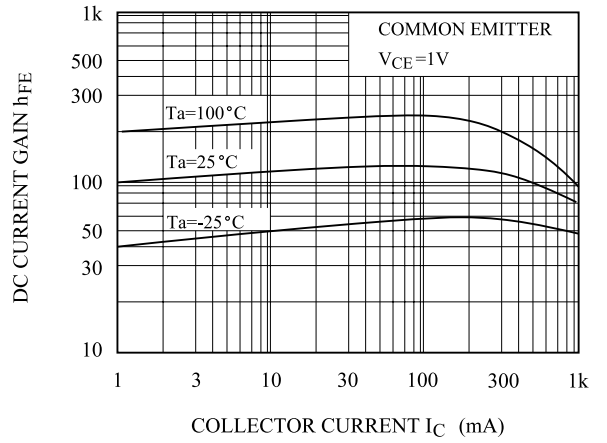
Note) : h_{FE} Classification D:150~300

MPS8050SC

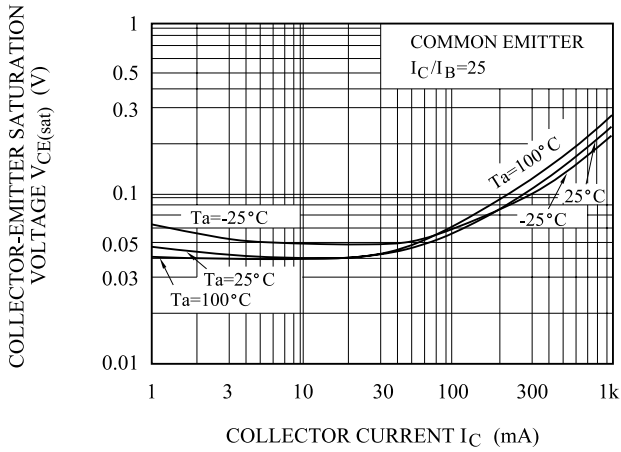
$I_C - V_{CE}$



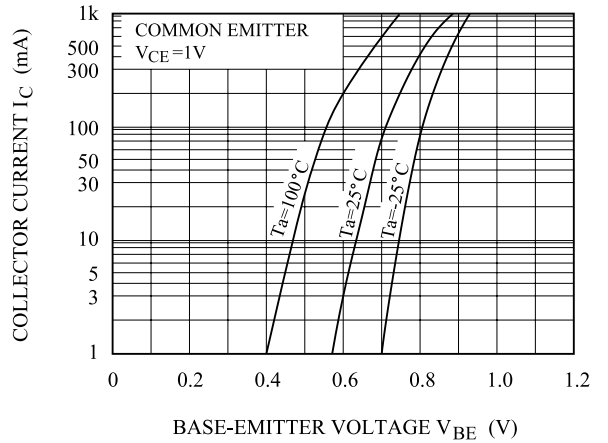
$h_{FE} - I_C$



$V_{CE(sat)} - I_C$



$I_C - V_{BE}$



$P_c - T_a$

